

# NCEP0135AK

## **NCE N-Channel Super Trench Power MOSFET**

### **Description**

The NCEP0135AK uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{\text{DS(ON)}}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

#### **General Features**

V<sub>DS</sub> =100V,I<sub>D</sub> =35A

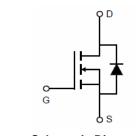
$$\begin{split} R_{DS(ON)} = &18m\Omega \text{ (typical) } \textcircled{@} \text{ } V_{GS} = &10V \\ R_{DS(ON)} = &22m\Omega \text{ (typical) } \textcircled{@} \text{ } V_{GS} = &4.5V \end{split}$$

- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 150 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

### **Application**

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!
100% ΔVds (ESTED!







Marking and pin assignment



TO-252-2L top view

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP0135AK	NCEP0135AK	TO-252-2L	-	-	-

### Absolute Maximum Ratings (T<sub>C</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	100	V
Gate-Source Voltage	V <sub>G</sub> s	±20	V
Drain Current-Continuous (Silicon Limited)	I <sub>D</sub>	35	А
Drain Current-Continuous(T <sub>C</sub> =100°C)	I <sub>D</sub> (100℃)	24.7	Α
Pulsed Drain Current (Package Limited)	I <sub>DM</sub>	180	Α
Maximum Power Dissipation	P <sub>D</sub>	110	W
Derating factor		0.73	W/℃
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	200	mJ
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 175	$^{\circ}$



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### **Thermal Characteristic**

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{ heta JC}$	1.36	°C/W
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Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

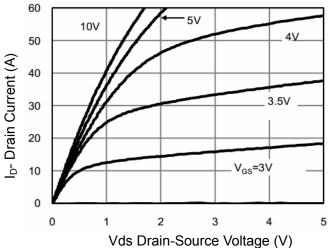
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	100		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V,V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS},I_{D}=250\mu A$	1.2	2.0	2.8	V
Drain-Source On-State Resistance	В	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-7	18	23	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A	-	22	27	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =20A	-	35	-	S
Dynamic Characteristics (Note4)		0,				
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =50V,V <sub>GS</sub> =0V,	-	1600	-	PF
Output Capacitance	Coss	$V_{DS}$ =50V, $V_{GS}$ =0V, $F=1.0MHz$	_	139	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	r- Huivinz	_	11	-	PF
Switching Characteristics (Note 4)		0,0				
Turn-on Delay Time	t <sub>d(on)</sub>		-	6	-	nS
Turn-on Rise Time	tr	$V_{DD}$ =50 $V$ , $I_D$ =20 $A$	_	2	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10 $V$ , $R_{G}$ =1.6 $\Omega$	-	18	-	nS
Turn-Off Fall Time	t <sub>f</sub>		_	2	-	nS
Total Gate Charge	$Q_g$	V -50V/I -20A	-	26	-	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =50V, $I_D$ =20A, $V_{GS}$ =10V	-	7.4		nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> -10V	_	3.8		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	$V_{SD}$	V <sub>GS</sub> =0V,I <sub>S</sub> =35A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	35	Α
Reverse Recovery Time	t <sub>rr</sub>	$T_J = 25^{\circ}C, I_F = 20A$	-		26	nS
Reverse Recovery Charge	Qrr	di/dt = $500A/\mu s^{(Note3)}$			98	nC

### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25  $^{\circ}\mathrm{C}$  ,V\_DD=20V,V\_G=10V,L=0.5mH,Rg=25 $\Omega$







**Figure 1 Output Characteristics** 

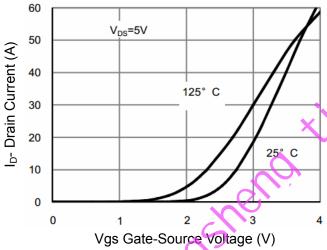
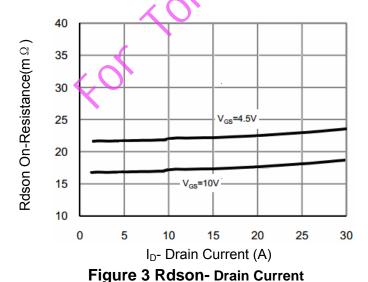


Figure 2 Transfer Characteristics



2.2

OUT 1.8

1.8

V<sub>GS</sub>=10V

I<sub>D</sub>=20A

1.2

V<sub>GS</sub>=4.5V

I<sub>D</sub>=20A

1.2

V<sub>GS</sub>=4.5V

I<sub>D</sub>=20A

1.5

T<sub>J</sub>-Junction Temperature(°C)

Figure 4 Rdson-Junction Temperature

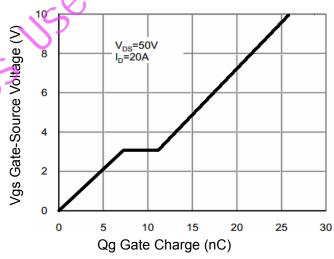


Figure 5 Gate Charge

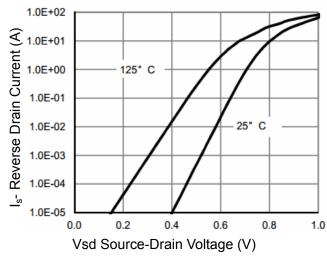


Figure 6 Source- Drain Diode Forward



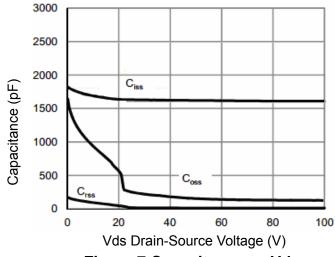


Figure 7 Capacitance vs Vds

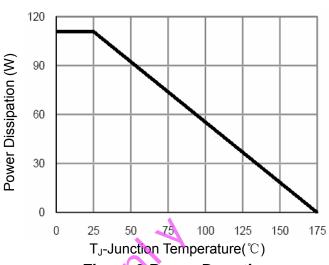


Figure 9 Power De-rating

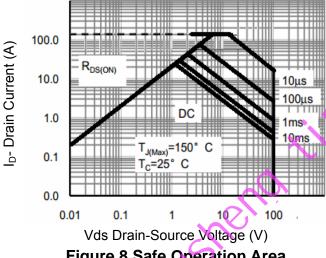


Figure 8 Safe Operation Area

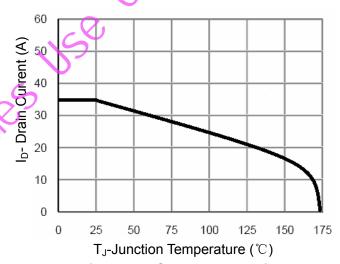


Figure 10 Current De-rating

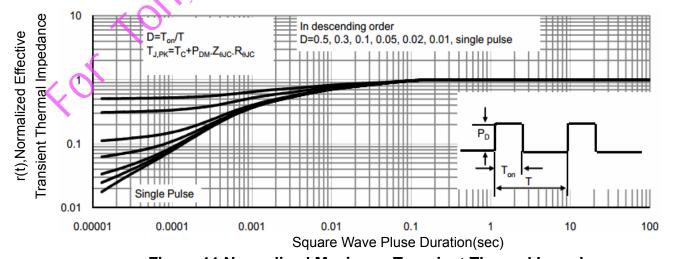
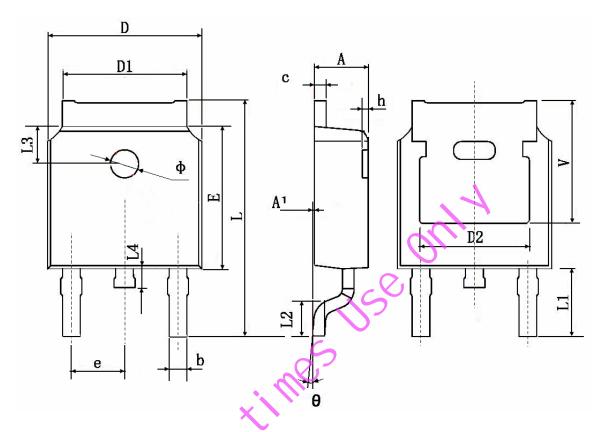


Figure 11 Normalized Maximum Transient Thermal Impedance

**Pb Free Product** 



# **TO-252 Package Information**



Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D 🔏	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2 🌈	4.83	TYP.	0.190 TYP.		
<b>∠</b> €	6.000	6.200	0.236	0.244	
e	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Φ	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350	TYP.	0.211 TYP.		



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